

PACKAGE DIMENSION	INTERNAL CIRCUIT DIAGRAM
<p style="text-align: center;">LMD5712CX-XX LIGITEK</p>	<p style="text-align: center;">LMD5712CX-XX</p>
<p>NOTE: All Dimension Are In Millimeters And (Inch) Tolerance Is <math>\pm 0.25(0.01)</math> Unless Otherwise Noted</p>	

**• Connection To Electrical Schematic**

<i>Electrical Connection</i>			
PIN NO.	LMD5712CX-XX		PIN NO.
1	Cathode Row	5	11
2	Cathode Row	7	12
3	Anode Column	2	13
4	Anode Column	3	14
5	Cathode Row	4	
6	Anode Column	5	
7	Cathode Row	6	
8	Cathode Row	3	
9	Cathode Row	1	
10	Anode Column	4	

• Part Selection And Application Information ( Ratings At 25°C Ambient)

PART NO	CHIP		common cathode or anode	$\lambda_P$ (nm)	$\Delta\lambda$ (nm)	Electrical					IV-M
	material	emitted				Vf(v)			Iv(mcd)		
						Min	Typ	Max	Min	Typ	
LMD5712CG-XX	GaP	Green	Column Anode Row Cathode	565	30	1.7	2.1	2.8	2.5	4.2	2:1
LMD5712CE-XX	GaAsP/GaP	Orange		635	45	1.7	2.0	2.8	2.5	4.5	2:1
LMD5712CSR-X	GaAlAs	Red		660	20	1.5	1.7	2.4	6.0	10	2:1

• Absolute Maximum Rating (Ta=25°C)

Parameter	Red		Green		Yellow		Orange		Unit	Remark
Forward Current Per Chip	SR			G				E		
	40			30				30	mA	
Peak Current Per Chip (Duty 1/10, 0.1MS Pulse Width)	200			120				120	mA	
Power Dissipation Per Chip	110			100				100	mW	
Derating Linear From 25°C Per Chip	0.45			0.45				0.45	mA/ °C	
Reverse Current Per Any Chip	10			10				10	μA	
Operating Temperature	-25°C TO +85°C									
Storage Temperature	-25°C TO +85°C									

Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260°C

• Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Dot	Iv	mcd	If=10mA
Peak Emission Wavelength	$\lambda_P$	nm	If=20mA
Spectral Line Half-Width	$\Delta\lambda$	nm	If=20mA
Reverse Current Any Chip	Ir	μA	Vr=5V
Luminous Intensity Matching Ratio	IV-M		